



Influence of hydrogen plasma treatment on charge storage characteristics in high density tungsten nanocrystal nonvolatile memory

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ABSTRACT

This study focuses on the influence of a hydrogen plasma treatment on electrical properties of tungsten nanocrystal nonvolatile memory. The X-ray photon emission spectra show that, after the hydrogen plasma treatment, a change in binding energy occurs such that Si^{x+} and Si^{y+} peaks appear at a position that is shifted about 2.3 and 3.3 eV from Si^{0+} in Si 2p spectra. This indicates that Si dangling bonds are passivated to form a Si–H bond structure in the SiO_2 . Furthermore, the transmission electron microscopy shows cross-sectional and plane-view for the nanocrystal microstructure after the hydrogen plasma treatment. Electrical measurement analyses show improved data retention because the hydrogen plasma treatment enhances the quality of the oxide surrounding the nanocrystals. The endurance and retention properties of the memory device are improved by about 36% and 30%, respectively.

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1. Introduction

Conventional nonvolatile memory (NVM, flash memory) suffers from certain limitations during continual scaling of device structures [1]. Therefore, in recent years nanocrystal (NC) nonvolatile memory devices have been investigated as a method to overcome these drawbacks. Because discrete trap storage nodes act as the charge center of NC nonvolatile memory devices, they can effectively avoid data loss in terms of reliability when scaling down such devices [2].

Among various NC nonvolatile memories [3–5], metal NCs are good candidates for improving the retention property and charge storage ability [6] due to their high work function, which provides a lower potential well compared to the silicon substrate. Tungsten (W) NC was chosen because, besides its high work function (4.9 eV), thermal stability is suitable for the process thermal budget [7–9]. Moreover, for nanoscale devices, the density of nanocrystals is an issue because the memory window is dependent on the NC density. High density is helpful to scale down the device structure. However, if the density of NCs is very high, then the quality of the oxide which surrounds the NCs will be critical because the electrons stored in NCs will escape easily by trap tunneling if the oxide quality is not sufficient. When NCs are very close to each other [10,11], there is a

tradeoff between high NC density and good reliability for nano-NVM application. In order to achieve both high density and good reliability, using high-pressure hydrogen treatment with high temperature annealing (700–900 °C) has proven to be a valid method to improve the oxide surrounding NCs [12,13]. Unfortunately, metal NCs and metal control gates cannot endure this temperature treatment. Hence, a hydrogen plasma treatment is proposed for W NC nonvolatile memory as an alternative method to passivate the defects in the surrounding oxide and improve its quality. The advantages of this method are a simple fabrication process and a low thermal budget.

2. Experiment

The process flow and the memory structure for this study are shown in Fig. 1. The W NC NVM capacitor structure was fabricated on single-crystal 6 in. (100) oriented P-type silicon. After the standard RCA cleaning, wafers went through a thermal oxidative process in an atmospheric pressure chemical vapor deposition furnace to form a 5 nm thick dry SiO_2 layer that serves as a tunnel oxide. Afterward, a 4 nm thick tungsten silicide (WSi_2) thin film was deposited onto the tunnel oxide by sputtering at room temperature with argon plasma 50 sccm (sccm denotes cubic centimeter per minute at standard temperature and pressure) and a DC power of 100 W. Subsequently, a 6 nm thick amorphous silicon (a-Si) layer was deposited by the same system with argon plasma 30 sccm and a RF power of 100 W. After the deposition of this WSi_2 /a-Si double layer structure, high temperature

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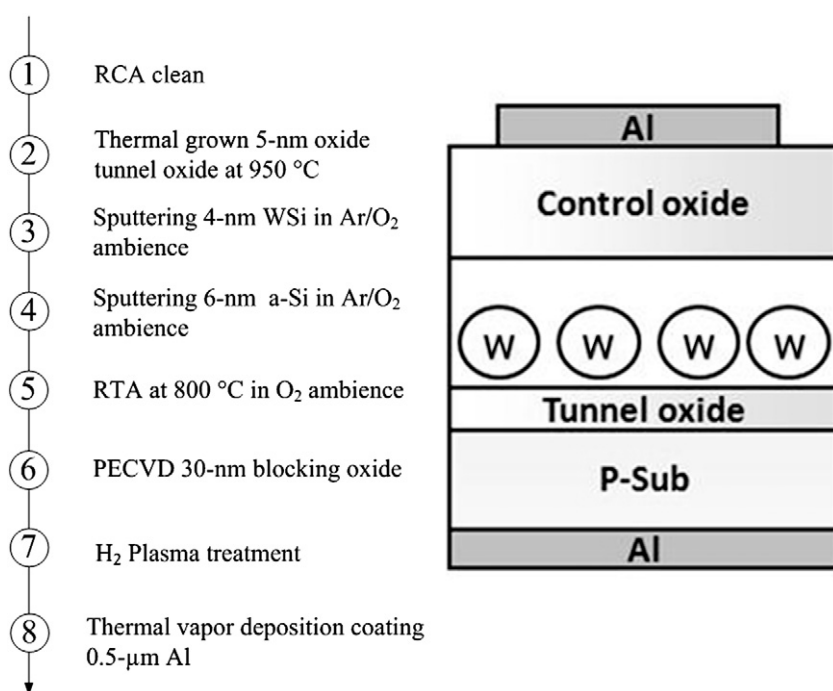


Fig. 1. Process flow and W nanocrystal NVM structure.

thermal oxidation was performed in the Rapid Thermal Annealing (RTA) system in oxygen ambient. RTA oxidation at 800 °C for 60 s is required to allow the WSi_2 layer to form W NCs, which then embed between the tunnel oxide and the control oxide. Afterwards, a 30 nm thick SiO_2 layer was deposited by a plasma enhanced chemical vapor deposition system to form a control oxide layer. For comparison, some of the samples were treated with hydrogen plasma for 30 min by high density plasma chemical vapor deposition at 200 W of plasma power and 200 sccm gas flow rate at 300 °C. The standard sample was plasma treated, whereas the control sample was used as reference without treatment, and will be referred to as standard and control samples hereafter. Finally, the top and the bottom Al electrodes were patterned by a shadow mask to form a metal–oxide–insulator–oxide–silicon structure. The aluminum was deposited by a thermal evaporator system with a thickness of 500 nm. Transmission electron microscope (TEM) analysis and X-ray photoelectron spectroscopy (XPS) were adopted for the microstructure and the chemical material analyses of nanoparticles. The cross-sectional TEM sample was prepared by focused ion beam process using a SII Nanotechnology Incorporated SMI 3050 system. The plane-view TEM sample was prepared by first polishing the sample thickness down to around 100 μm with a grinding polishing machine. Then the sample thickness is further reduced to about 10 μm by milling with Ar^+ ions using a Gatan Model 691 precise ion polishing system. The high-resolution TEM was carried out using a JEOL JEM-2100F system operated at 200 kV. XPS analysis was performed using a VG Scientific Microlab 310F with 300 W Al $K\alpha$ (1486.6 eV) as the X-ray source and was calibrated by a C 1s peak at 284.5 eV. The functions used for deconvolution are naturally broad and can be approximated with finite Gaussian or Lorentzian shape or a combination by XPSPEAK41 software. The electrical characteristics of capacitance–voltage (C–V) hysteresis were also measured by an HP4284 Precision LCR Meter with a high frequency of 100 kHz.

3. Results and discussion

Fig. 2(a) and (b) shows the TEM image cross-sectional and plane-view for the proposed device. The TEM image analyses show that the

average diameter of nanocrystals is approximately 8 nm and the area density can be estimated to be about $2.5 \times 10^{12} \text{ cm}^{-2}$. After going through the process indicated above, a high density of NCs was gained appropriate for 32–22 nm device applications.

Fig. 3(a) and (b) shows the Si 2p spectra of the control and standard sample, performed by a monochromatic Al $K\alpha$ (1486.6 eV) X-ray. In Fig. 3(a), the transition region spectra between Si^{0+} and Si^{4+} are not observed in the SiO_2 , which had not been exposed to the hydrogen plasma. Therefore, deconvolution of the spectra was carried out assuming that only Si^{0+} and Si^{4+} peaks exist in the Si 2p spectra for the unexposed SiO_2 [14–17]. In contrast, the SiO_2 which had been exposed to the hydrogen plasma exhibited transition region spectra between Si^{0+} and Si^{4+} in the Si 2p spectra, shown in Fig. 3(b). These transition region spectra could not be deconvoluted as Si^{3+} , Si^{2+} and Si^{1+} . It has been reported that Si^{x+} and Si^{y+} spectra which have shifted about 2.3 and 3.3 eV from Si^{0+} will appear in Si 2p spectra if a Si–H bond structure exists in the SiO_2 . Therefore, because our results exhibit just such transition spectra, the sample with hydrogen plasma treatment can be assumed to produce the Si–H bonding and chemical shifts for Si–H bonding configurations, as shown in Fig. 3(c). In addition, the shift to lower energy and the increase in the intensity of the Si^{0+} peak and the presence of the Si^{2+} after hydrogen plasma treatment are caused by the Si and Si– Si_2O_2 reduction from weak Si– O_4 bonds [18–20]. Moreover, W 4f core-level photoemission spectra of the control and standard samples both consist of the two main peaks of W 4f $^{7/2}$ (31.4 eV) and W 4f $^{5/2}$ (33.5 eV), as shown in Fig. 4(a) and (b). The small peak at a position 35.2 eV is the peak of WO_3 of W 4f bonding [21,22]. Some of the W was probably oxidized during the rapid thermal annealing in the oxygen ambient because the solid solubility of O atoms within W material is extremely small [23], and O atoms cannot exist in W nanocrystals except if there is absolute oxidation of tungsten. Therefore, the position of WO_3 will be on the surface of the W nanocrystals. The W 4f spectra of the control and standard sample are very similar. In addition, in our experiment, the hydrogen plasma treatment is a post-treatment after the W nanocrystal formation. Therefore, it is unlikely that the W 4f spectra of the control and standard sample would show major differences, as the treatment does not influence the W nanocrystal formation.

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